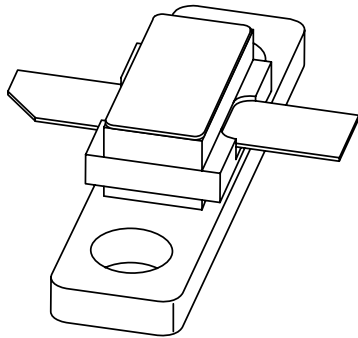


# DATA SHEET



## **BLS3135-10** Microwave power transistor

Product specification

2000 Feb 01

# Microwave power transistor

# BLS3135-10

### FEATURES

- Suitable for short and medium pulse applications
- Internal input and output matching networks for an easy circuit design
- Emitter ballasting resistors improve ruggedness
- Gold metallization ensures excellent reliability
- Interdigitated emitter-base structure provides high emitter efficiency
- Multicell geometry improves power sharing and reduces thermal resistance.

### APPLICATIONS

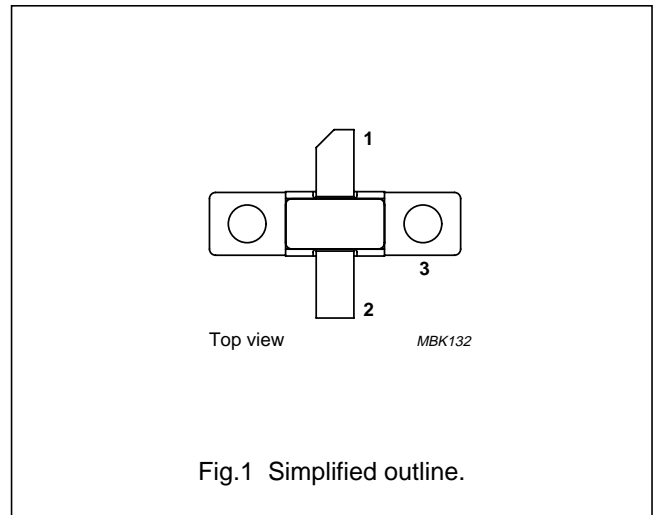
- Common base class-C pulsed power amplifier for radar applications in the 3.1 to 3.5 GHz range.

### DESCRIPTION

NPN silicon planar epitaxial microwave power transistor in a 2-lead rectangular flange package with a ceramic cap (SOT445C) with the common base connected to the flange.

### PINNING - SOT445C

PIN	DESCRIPTION
1	collector
2	emitter
3	base; connected to flange



### QUICK REFERENCE DATA

RF performance at  $T_h = 25\text{ }^\circ\text{C}$  in a common base class-C test circuit.

MODE OF OPERATION	f (GHz)	$V_{CB}$ (V)	$P_L$ (W)	$G_p$ (dB)	$\eta_c$ (%)
Pulsed class-C	3.1 to 3.5	40	$\geq 10$	typ. 9	typ. 40

### WARNING

#### Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

## Microwave power transistor

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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	75	V
$V_{CES}$	collector-emitter voltage	$R_{BE} = 0$	–	75	V
$V_{EBO}$	emitter-base voltage	open collector	–	2	V
$I_{CM}$	peak collector current	$t_p \leq 100 \mu\text{s}$ ; $\delta \leq 10\%$	–	1.5	A
$P_{tot}$	total power dissipation	$t_p = 100 \mu\text{s}$ ; $\delta = 10\%$ ; $T_h = 25 \text{ }^\circ\text{C}$	–	34	W
$T_{stg}$	storage temperature		–65	+200	$^\circ\text{C}$
$T_j$	operating junction temperature		–	200	$^\circ\text{C}$
$T_{sld}$	soldering temperature	up to 0.2 mm from ceramic cap; $t \leq 10 \text{ s}$	–	235	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$Z_{th\ j-h}$	thermal impedance from junction to heatsink	$t_p = 100 \mu\text{s}$ ; $\delta = 10\%$ ; note 1	5.2	K/W
		$t_p = 200 \mu\text{s}$ ; $\delta = 10\%$ ; note 1	5.8	K/W
		$t_p = 300 \mu\text{s}$ ; $\delta = 10\%$ ; note 1	6.3	K/W

**Note**

1. Equivalent thermal impedance under pulsed microwave operating conditions.

**CHARACTERISTICS** $T_j = 25 \text{ }^\circ\text{C}$  unless otherwise specified.

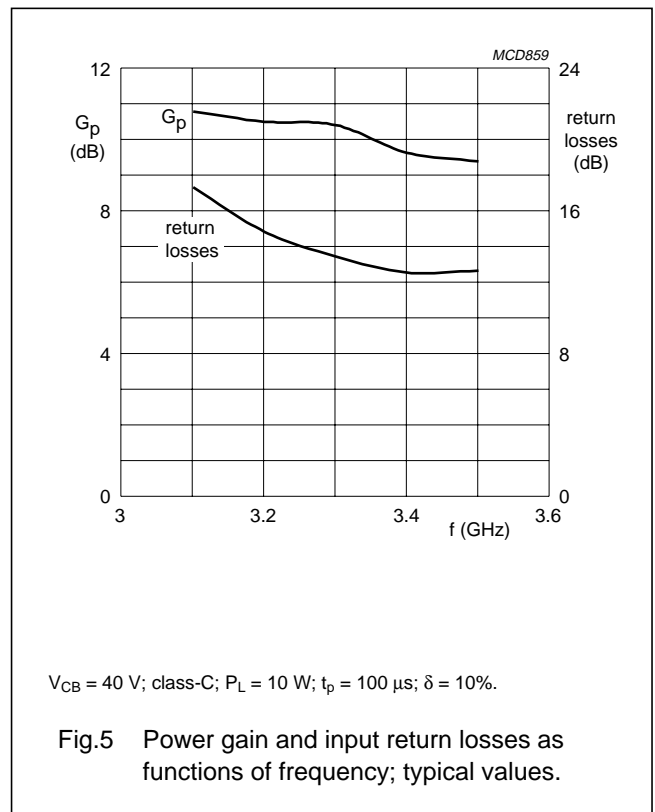
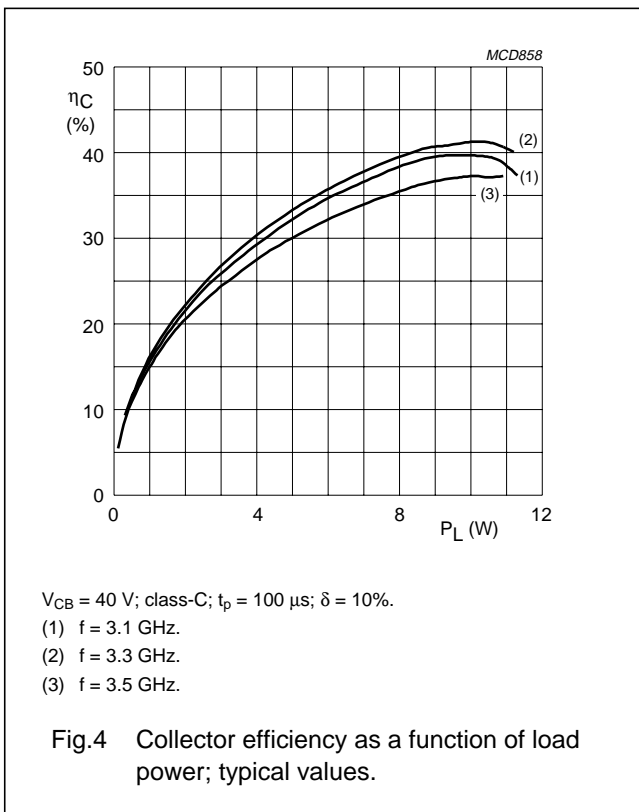
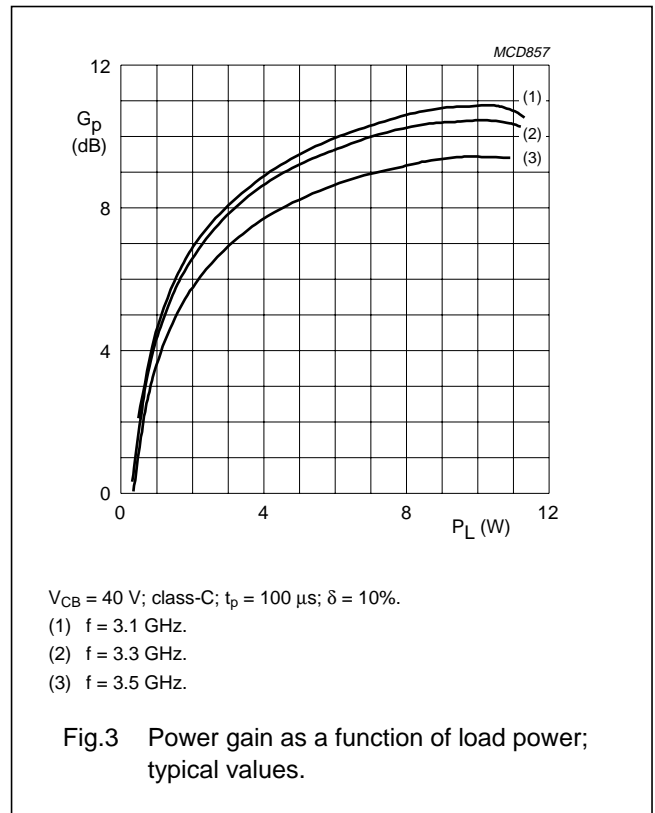
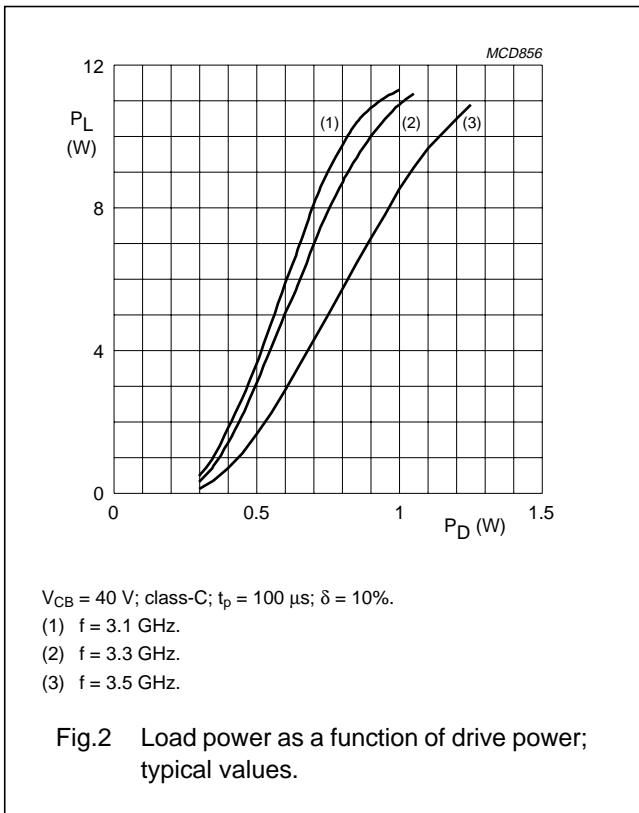
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 2.5 \text{ mA}$ ; open emitter	75	–	V
$V_{(BR)CES}$	collector-emitter breakdown voltage	$I_C = 2.5 \text{ mA}$ ; $V_{BE} = 0$	75	–	V
$I_{CBO}$	collector leakage current	$V_{CB} = 40 \text{ V}$ ; $I_E = 0$	–	0.3	mA
$I_{CES}$	collector leakage current	$V_{CE} = 40 \text{ V}$ ; $V_{BE} = 0$	–	0.5	mA
$I_{EBO}$	emitter leakage current	$V_{EB} = 1.5 \text{ V}$ ; $I_C = 0$	–	0.1	mA
$h_{FE}$	DC current gain	$V_{CE} = 5 \text{ V}$ ; $I_C = 0.25 \text{ A}$	40	–	

**APPLICATION INFORMATION**RF performance at  $T_h = 25 \text{ }^\circ\text{C}$  in a common-base test circuit.

MODE OF OPERATION	f (GHz)	$V_{CE}$ (V)	$P_L$ (W)	$G_p$ (dB)	$\eta_c$ (%)
Class-C; $t_p = 100 \mu\text{s}$ ; $\delta = 10\%$	3.1 to 3.5	40	$\geq 10$	$\geq 7.5$ typ. 9	$\geq 35$ typ. 40

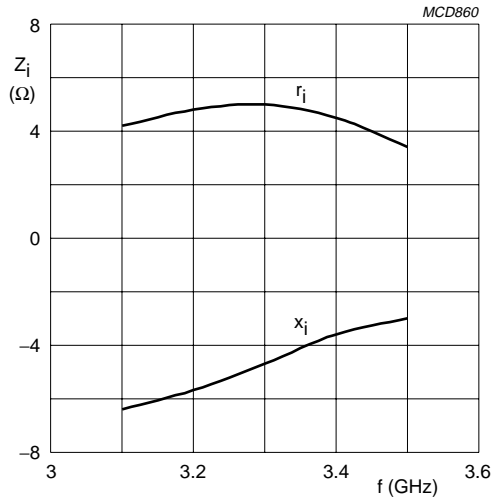
Microwave power transistor

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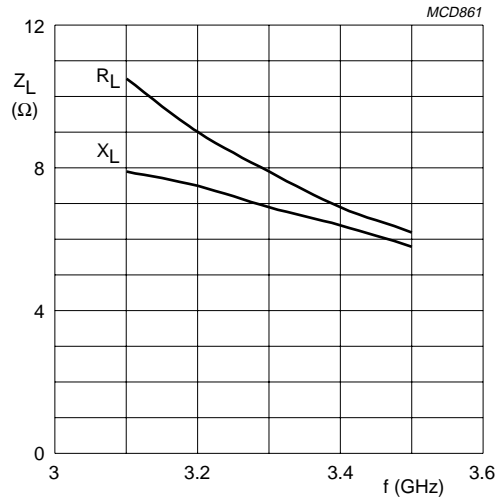
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$V_{CB} = 40$  V; class-C;  $P_L = 10$  W.

Fig.6 Input impedance as a function of frequency (series components); typical values.

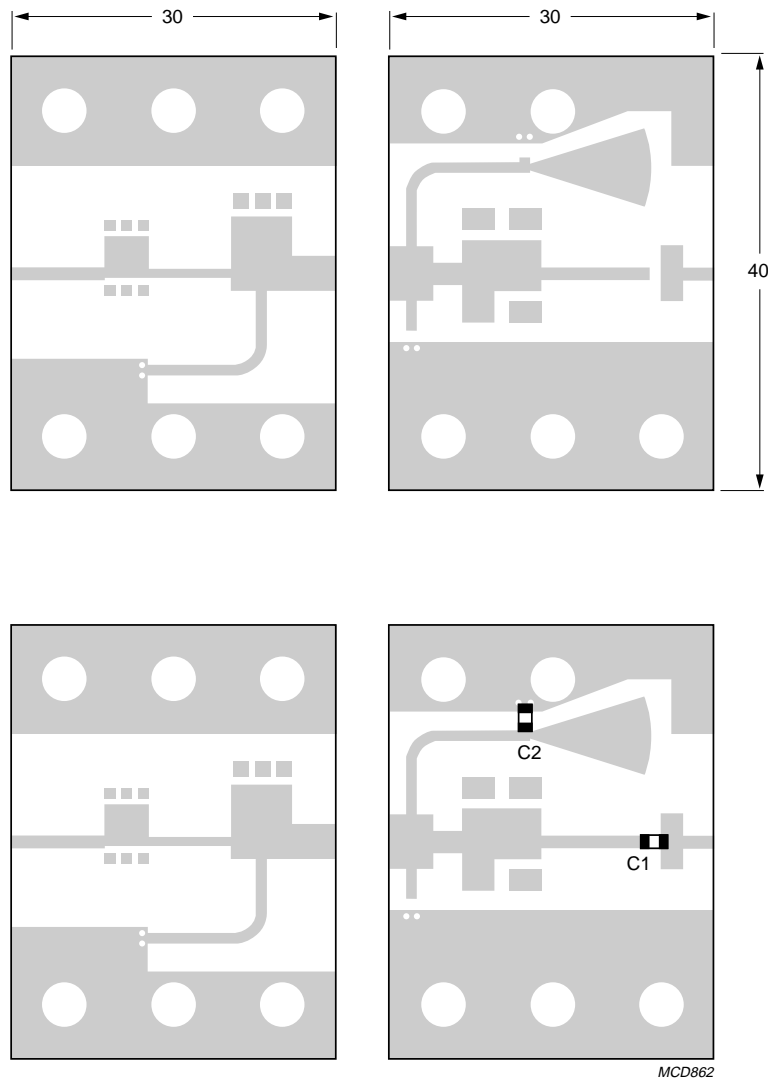


$V_{CB} = 40$  V; class-C;  $P_L = 10$  W.

Fig.7 Load impedance as a function of frequency (series components); typical values.

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Dimensions in mm.

The components are situated on one side of the copper-clad printed-circuit board with Duroid dielectric ( $\epsilon_r = 2.2$ ), thickness 0.38 mm. The other side is unetched and serves as a ground plane.

C1 = 10 pF (ATC 100A); C2 = 100 pF (ATC 100A).

Fig.8 Component layout for 3.1 to 3.5 GHz class-C test circuit.

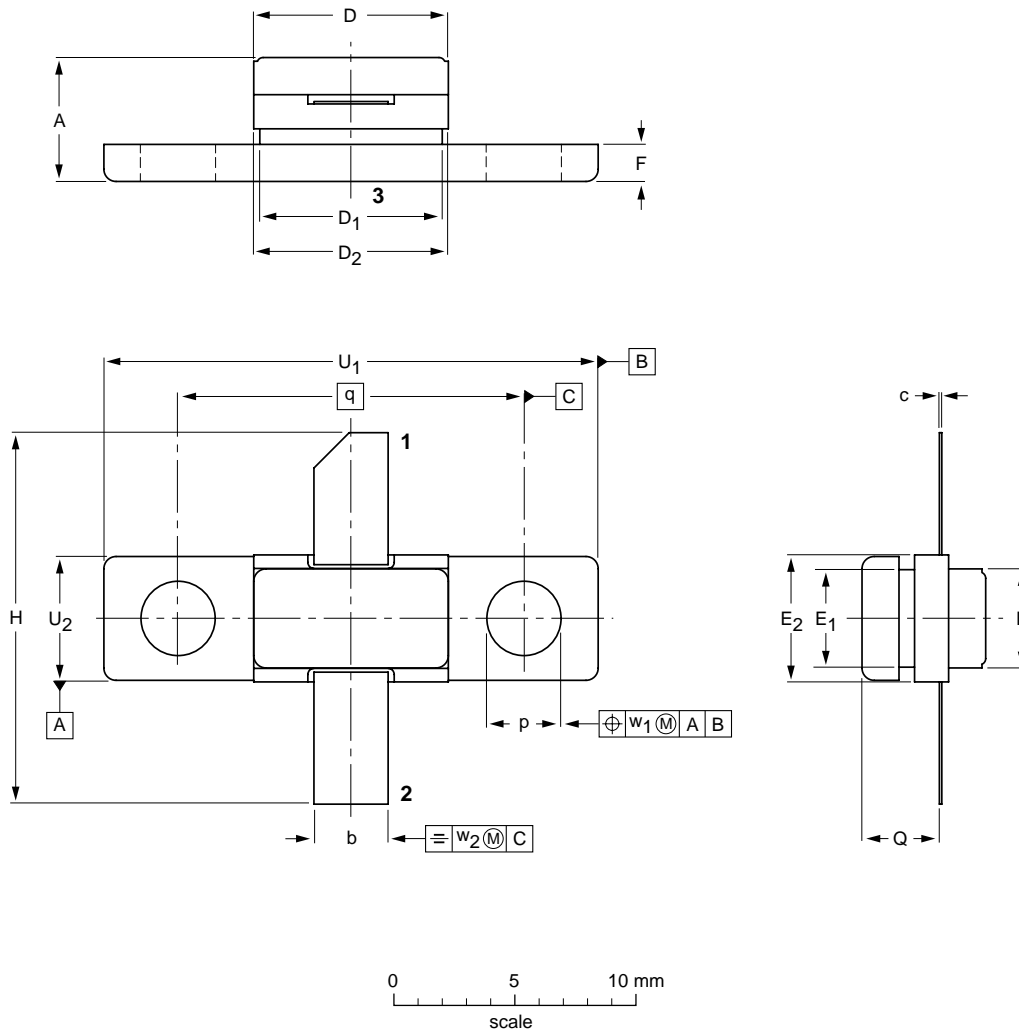
Microwave power transistor

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PACKAGE OUTLINE

Flanged hermetic ceramic package; 2 mounting holes; 2 leads

SOT445C



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	c	D	D <sub>1</sub>	D <sub>2</sub>	E	E <sub>1</sub>	E <sub>2</sub>	F	H	p	Q	q	U <sub>1</sub>	U <sub>2</sub>	w <sub>1</sub>	w <sub>2</sub>
mm	5.57 4.70	3.15 2.95	0.15 0.09	8.13 7.87	7.65 7.35	8.15 7.85	4.20 3.93	4.25 3.95	5.31 5.01	1.82 1.22	15.84 14.64	3.35 3.05	3.33 3.03	14.22	20.47 20.17	5.18 4.98	0.51	1.02

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT445C						97-05-23

## Microwave power transistor

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**DEFINITIONS**

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

**LIFE SUPPORT APPLICATIONS**

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.



Microwave power transistor

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**NOTES**

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# Philips Semiconductors – a worldwide company

**Argentina:** see South America

**Australia:** 3 Figtree Drive, HOMEBUSH, NSW 2140,  
Tel. +61 2 9704 8141, Fax. +61 2 9704 8139

**Austria:** Computerstr. 6, A-1101 WIEN, P.O. Box 213,  
Tel. +43 1 60 101 1248, Fax. +43 1 60 101 1210

**Belarus:** Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,  
220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773

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**Bulgaria:** Philips Bulgaria Ltd., Energoproject, 15th floor,  
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**China/Hong Kong:** 501 Hong Kong Industrial Technology Centre,  
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**Colombia:** see South America

**Czech Republic:** see Austria

**Denmark:** Sydhavnsgade 23, 1780 COPENHAGEN V,  
Tel. +45 33 29 3333, Fax. +45 33 29 3905

**Finland:** Sinikalliontie 3, FIN-02630 ESPOO,  
Tel. +358 9 615 800, Fax. +358 9 6158 0920

**France:** 51 Rue Carnot, BP317, 92156 SURESNES Cedex,  
Tel. +33 1 4099 6161, Fax. +33 1 4099 6427

**Germany:** Hammerbrookstraße 69, D-20097 HAMBURG,  
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**Hungary:** see Austria

**India:** Philips INDIA Ltd, Band Box Building, 2nd floor,  
254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,  
Tel. +91 22 493 8541, Fax. +91 22 493 0966

**Indonesia:** PT Philips Development Corporation, Semiconductors Division,  
Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510,  
Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

**Ireland:** Newstead, Clonskeagh, DUBLIN 14,  
Tel. +353 1 7640 000, Fax. +353 1 7640 200

**Israel:** RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,  
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

**Italy:** PHILIPS SEMICONDUCTORS, Via Casati, 23 - 20052 MONZA (MI),  
Tel. +39 039 203 6838, Fax +39 039 203 6800

**Japan:** Philips Bldg 13-37, Kohnan 2-chome, Minato-ku,  
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**Malaysia:** No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,  
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Tel. +31 40 27 82785, Fax. +31 40 27 88399

**New Zealand:** 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,  
Tel. +64 9 849 4160, Fax. +64 9 849 7811

**Norway:** Box 1, Manglerud 0612, OSLO,  
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**Pakistan:** see Singapore

**Philippines:** Philips Semiconductors Philippines Inc.,  
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Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

**Poland:** Al.Jerozolimskie 195 B, 02-222 WARSAW,  
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2092 JOHANNESBURG, P.O. Box 58088 Newville 2114,  
Tel. +27 11 471 5401, Fax. +27 11 471 5398

**South America:** Al. Vicente Pinzon, 173, 6th floor,  
04547-130 SÃO PAULO, SP, Brazil,  
Tel. +55 11 821 2333, Fax. +55 11 821 2382

**Spain:** Balmes 22, 08007 BARCELONA,  
Tel. +34 93 301 6312, Fax. +34 93 301 4107

**Sweden:** Kottbygatan 7, Akalla, S-16485 STOCKHOLM,  
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**Switzerland:** Allmendstrasse 140, CH-8027 ZÜRICH,  
Tel. +41 1 488 2741 Fax. +41 1 488 3263

**Taiwan:** Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,  
TAIPEI, Taiwan Tel. +886 2 2134 2886, Fax. +886 2 2134 2874

**Thailand:** PHILIPS ELECTRONICS (THAILAND) Ltd.,  
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**Turkey:** Yukari Dudullu, Org. San. Blg., 2.Cad. Nr. 28 81260 Umraniye,  
ISTANBUL, Tel. +90 216 522 1500, Fax. +90 216 522 1813

**Ukraine:** PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,  
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

**United Kingdom:** Philips Semiconductors Ltd., 276 Bath Road, Hayes,  
MIDDLESEX UB3 5BX, Tel. +44 208 730 5000, Fax. +44 208 754 8421

**United States:** 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,  
Tel. +1 800 234 7381, Fax. +1 800 943 0087

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